

AMENDMENT AND RESPONSE**PAGE 2**

Serial No.: 10/033,156

Filing Date: 10/25/2001

Attorney Docket No. 125.020US01

Title: SEALED NITRIDE LAYER FOR INTEGRATED CIRCUITS

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of claims:

1. (Previously presented) A method of forming a sealing nitride layer overlaying a oxide layer in a contact opening of an integrated circuit, the method comprising:

forming a second layer of nitride overlaying a first layer of nitride without any intervening layers between the first and second layers of nitride to form the sealing nitride layer, the second layer of nitride further overlaying and in contact with an exposed portion of a surface of a substrate in the contact opening and sidewalls of the contact opening; and

using reactive ion etching (RIE etch) without a mask to remove a portion of the second nitride layer adjacent the surface of the substrate in the contact opening to expose a portion of the surface of the substrate in the contact opening without removing portions of the second nitride layer covering the sidewalls of the contact opening.

2. (Original) The method of claim 1, wherein the second layer of nitride is formed by low pressure chemical vapor deposition.

3. (Original) The method of claim 1, wherein the second layer of nitride is formed by plasma enhanced chemical vapor deposition.

4. (Original) The method of claim 1, wherein, at least a portion of the first layer of nitride remains overlaying the oxide layer after the RIE etch is applied.

5. (Original) The method of claim 1, wherein the RIE etch is applied for a pre-determined amount of time.

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6. (Original) The method of claim 5, wherein the pre-determined amount of time is the time it takes to remove a portion of the second layer of nitride from the surface of the substrate in the contact opening.

7. (Previously presented) A method of forming an integrated circuit, the method comprising:

forming a layer of oxide over a surface of a substrate;

forming a first layer of nitride overlaying the layer of oxide;

forming a contact opening through the first layer of nitride and the oxide layer to expose a portion of the surface of the substrate;

forming a second layer of nitride overlaying the first layer of nitride, the second layer of nitride also overlaying the exposed portion of the surface of the substrate in the contact opening and sidewalls of the contact opening; and

using a reactive ion etch (RIE etch) without a mask on the substrate for a pre-determined amount of time to remove a portion of the second layer of nitride overlaying the surface of the substrate in the contact opening without removing the portions of the second nitride layer overlaying the sidewalls of the contact opening and without removing portions of the first nitride layer overlaying the oxide layer, wherein the oxide layer is sealed by the first and second nitride layers.

8. (Original) The method of claim 7, wherein the contact opening through the first nitride layer and the oxide layer is done with a dry etch with one mask to form an anisotropic contact opening.

9. (Original) The method of claim 7, wherein the oxide layer is thermally grown.

10. (Original) The method of claim 7, wherein the oxide layer is deposited.

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11. (Original) The method of claim 7, wherein the first and second layers of nitride are formed by low pressure chemical vapor deposition.

12. (Original) The method of claim 7, wherein the first and second layers of the nitride are formed by plasma enhanced chemical vapor deposition.

13. (Canceled)

14. (Previously presented) A method of forming semiconductor devices in an integrated circuit comprising:

forming a plurality of device regions of a first conductivity type in a substrate adjacent a surface of the substrate;

forming an oxide layer over a surface of a substrate;

patterning the oxide layer to expose pre-selected portions of the surface of the substrate;

forming a first layer of nitride overlaying the oxide layer and the exposed portions of the surface of the substrate;

implanting ions of a second conductivity type through the layer of nitride into the substrate to form device regions of the second conductivity type, wherein remaining portions of the oxide layer under the nitride layer selectively stop the ions from entering the substrate to selectively define edges of the device regions of the second conductivity type;

forming contact openings to expose a portion of each of the device regions of the first and second conductivity type in the substrate;

forming a second layer of nitride over the first layer of nitride, the second layer of nitride also overlaying the exposed portions of each of the device regions in their associated contact openings and sidewalls of each of the contact openings; and

exposing the substrate to a reactive ion etch (RIE etch) for a pre-determined amount of time to remove portions of the second layer of nitride adjacent a surface of each device region in an associated contact opening, wherein the substrate is not exposed to the RIE etch long enough to remove all of the portions of the second nitride layer overlaying the respective sidewalls of

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each of the contact openings and portions of the first layer of nitride overlaying the oxide layer so that the oxide layer remains sealed by the first and second layers of nitride.

15. (Original) The method of claim 14, wherein the contact openings made through the first nitride layer and the oxide layer to associated device regions are done with a dry etch with a single mask to form anisotropic contact openings.

16. (Original) The method of claim 14, wherein the first and second layers of nitride are formed by low pressure chemical vapor deposition.

17. (Original) The method of claim 14, wherein the first and second layers of the nitride are formed by plasma enhanced chemical vapor deposition.

18. (Canceled)

19-22. (Withdrawn)